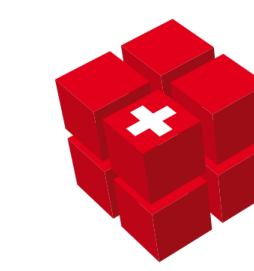


# In-plane strain effect on interface stress in Cu/W nano-multilayers



Empa

Materials Science and Technology



Javier F. Troncoso<sup>1</sup>, Giacomo Lorenzin<sup>1</sup>, Claudia Cancellieri<sup>1</sup>, Manura Liyanage<sup>2</sup>, Vladyslav Turlo<sup>1</sup>

[1] Empa - Swiss Federal Laboratories for Materials Science and Technology, Dübendorf and Thun, Switzerland

[2] Laboratory for Multiscale Mechanics Modeling, EPFL, Lausanne, Switzerland

e-mail: Vladyslav.Turlo@empa.ch

## INTRODUCTION

- The copper/tungsten (Cu/W) system combines the good electrical and thermal properties of Cu with the excellent mechanical properties of W.
- Due to complete immiscibility and incompatibility between Cu and W, interface effects play an important role in Cu/W multilayers and the resulting material properties can be tailored for industrial applications through microstructural and interfacial design.
- Interface stress is one of the fundamental thermodynamics parameters related to interface boundaries in strict relation to interface energy.
- Interface stress is the variation of interface energy with the applied in-plane strain, i.e., interface stress is the work needed to deform the pre-existing interface area elastically, thus providing information about the stability and equilibration of boundaries.

## OBJECTIVES

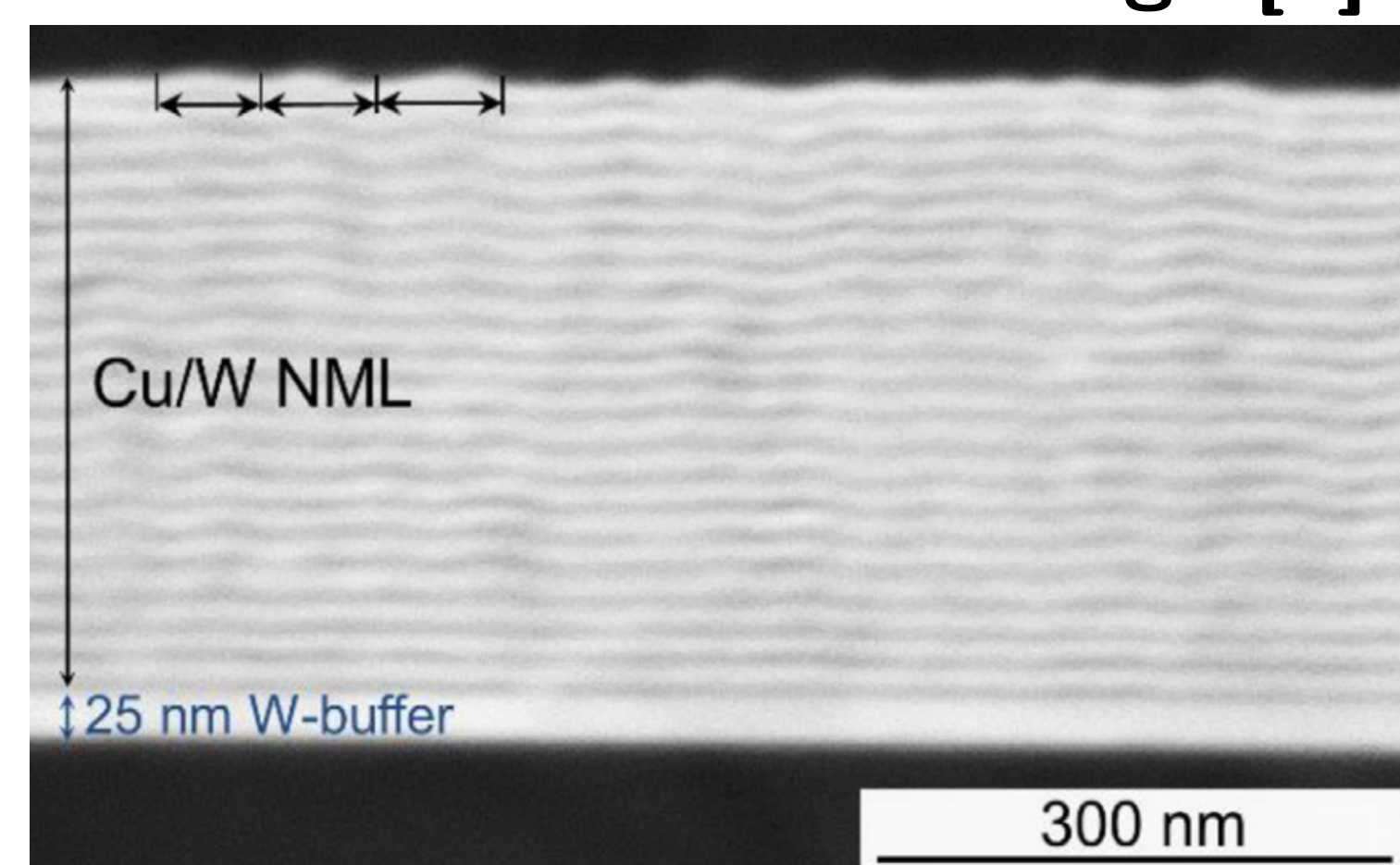
- Combination of experimental observations and modeling approaches to investigate the relationship between in-plane strain and interface stress, using Cu / W nano-multilayers as a model system.

## EXPERIMENTAL DETAILS

Cu/W nano-multilayers:

- are produced by DC magnetron sputtering
- composed of alternating 10 nm Cu and 10 nm W layers
- demonstrate Cu{111}/W{110} out-of-plane orientation relation
- develop different in-plane strain depending on Ar pressure

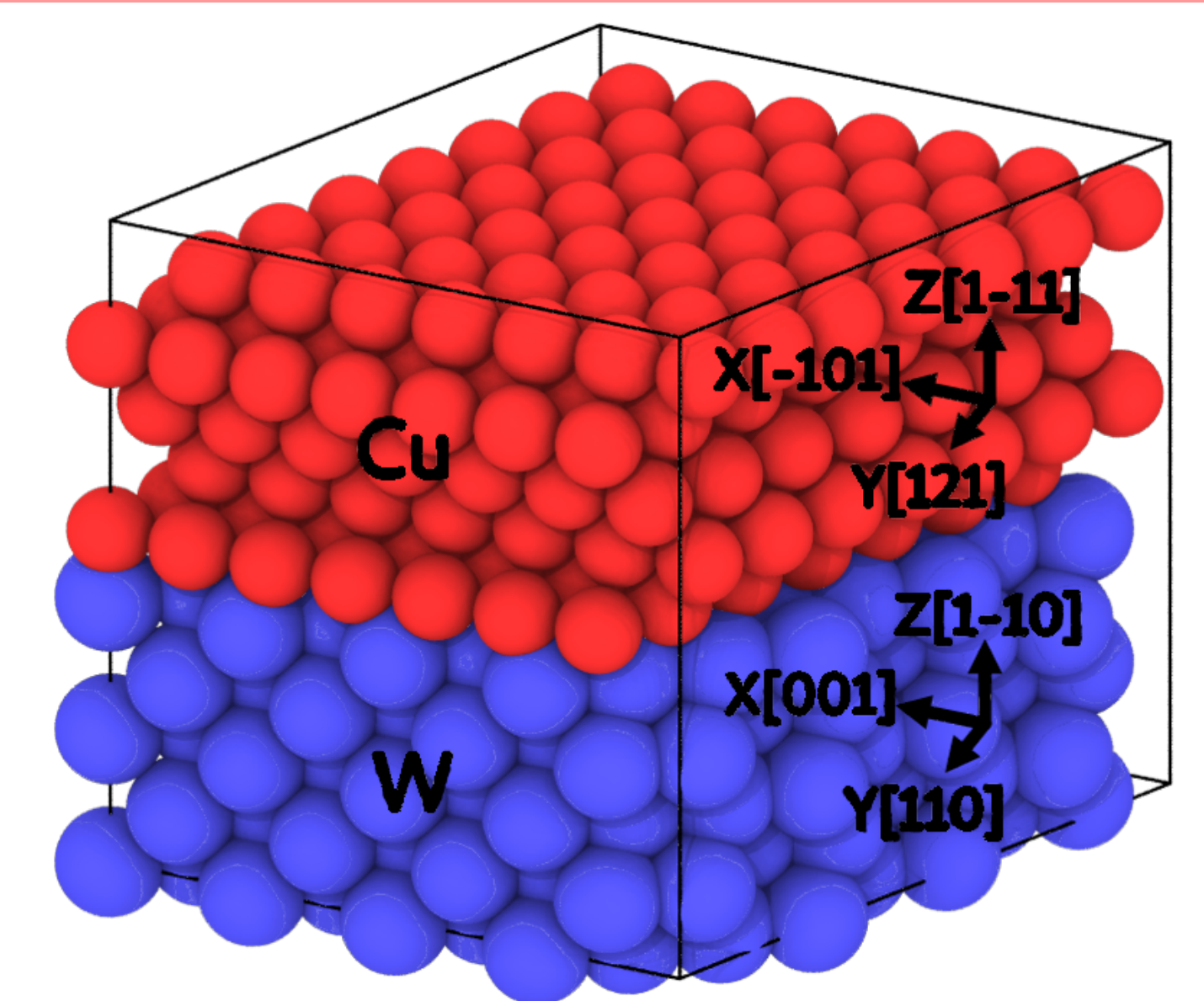
Cross-sectional SEM image [1]



## AB INITIO CALCULATIONS

Density functional theory (DFT) calculations are done using:

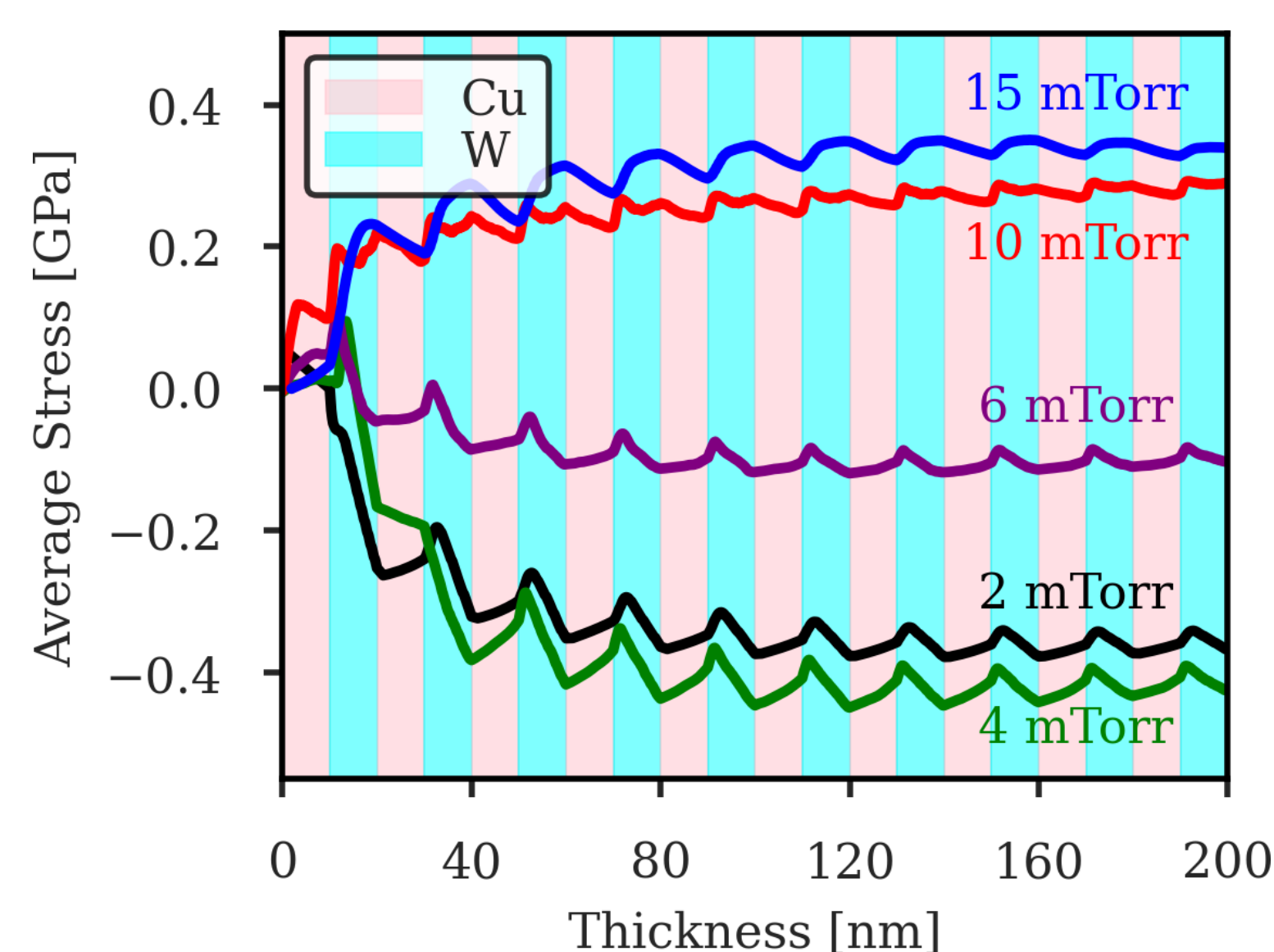
- the bilayer containing 245 Cu atoms and 200 W atoms generated via the CellMatch code [2].
- the CP2K code [3].
- the Goedecker–Teter–Hutter pseudopotential [4]



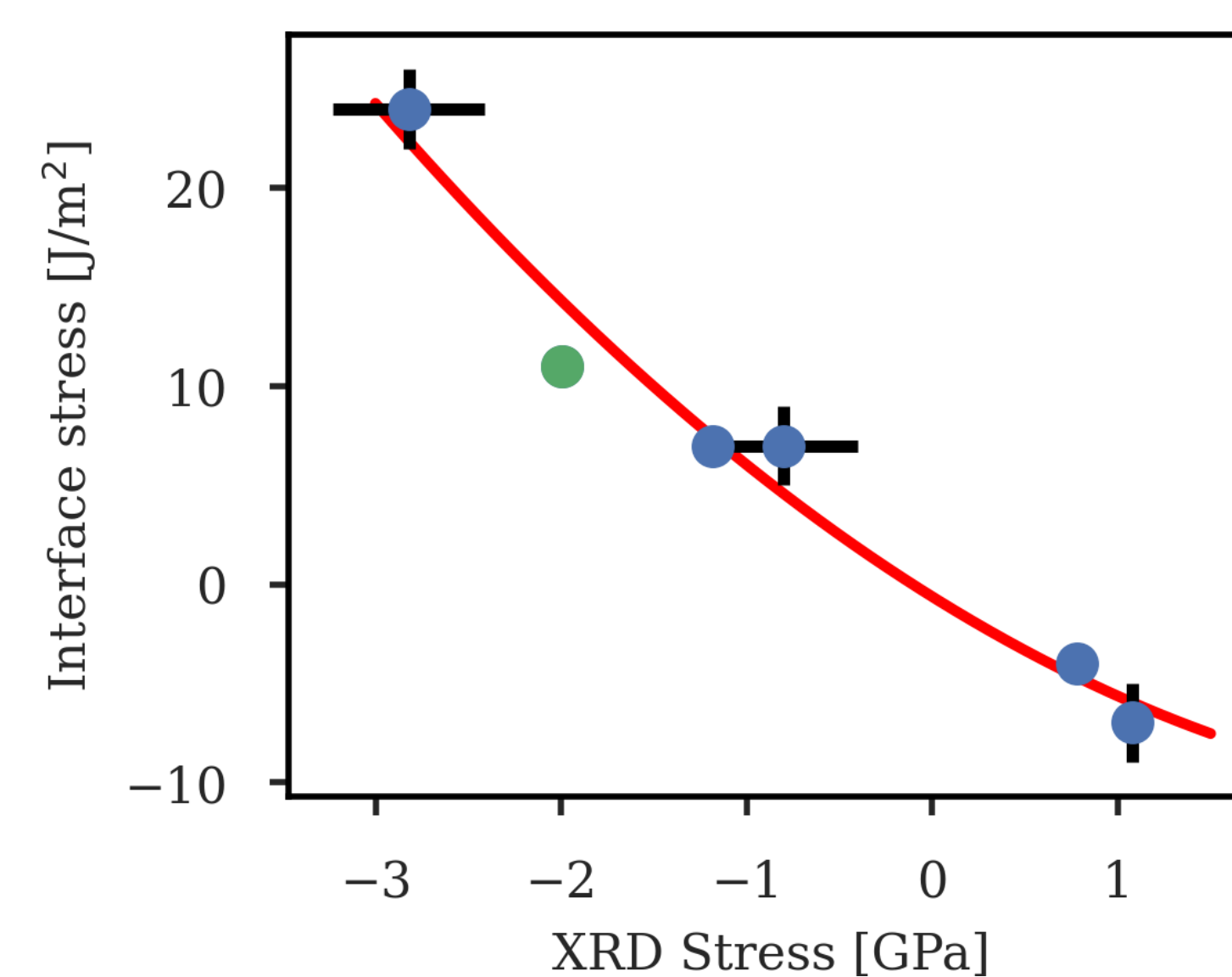
## RESULTS

### EXPERIMENTS

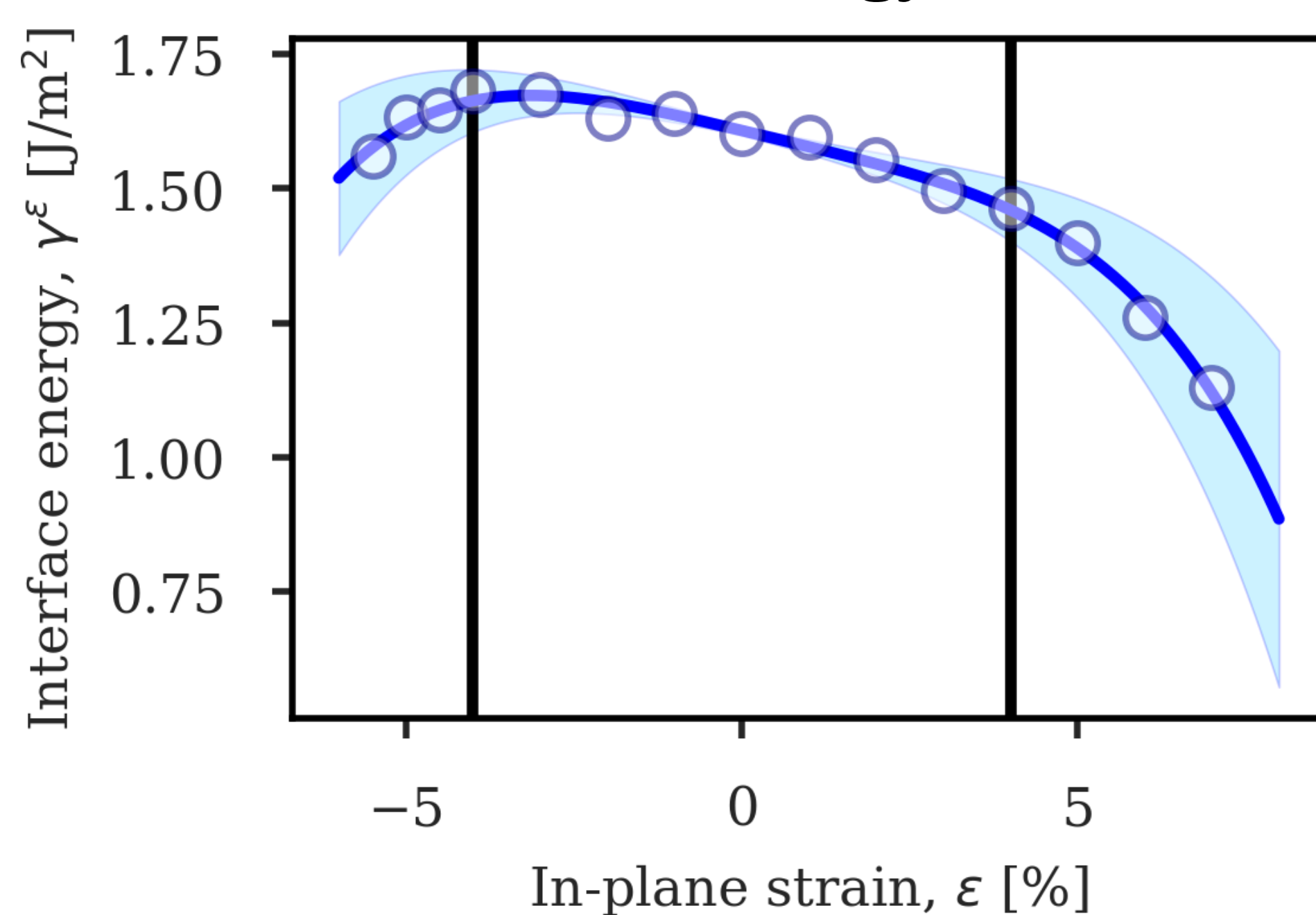
#### A Local Stress in multilayers



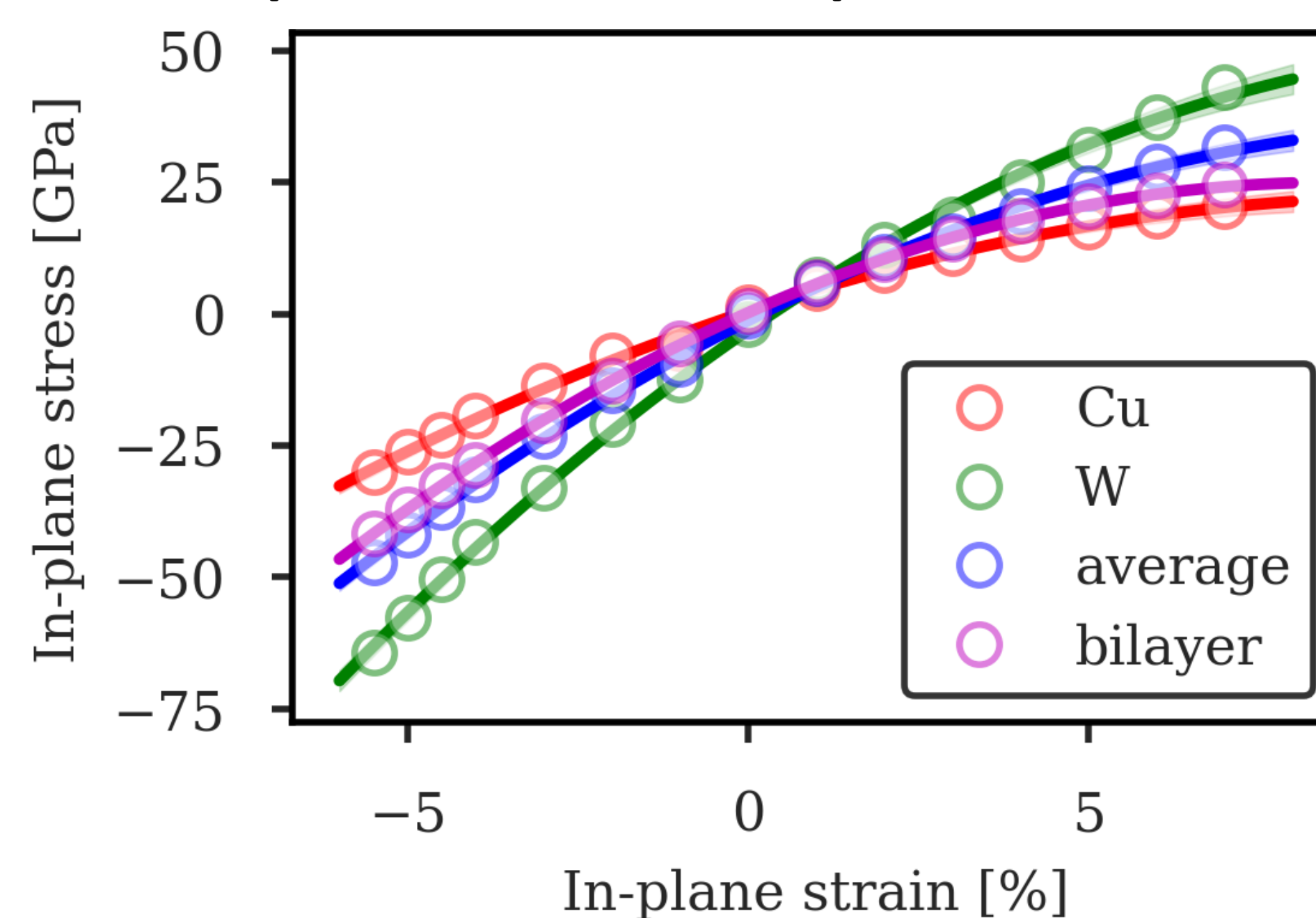
#### B Interface Stress



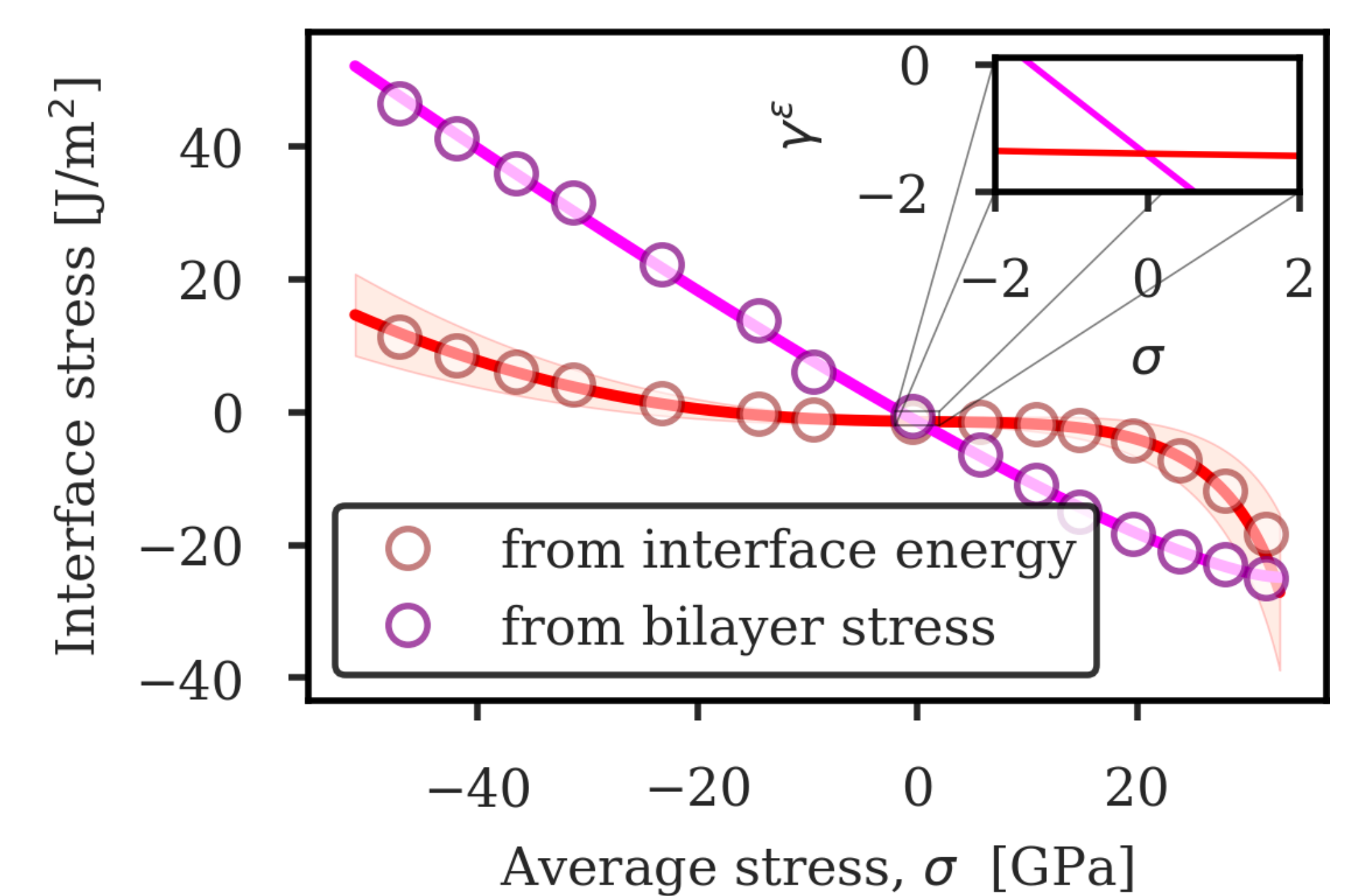
#### C Interface energy



#### D In-plane strain vs in-plane stress



#### E Interface Stress



Interface stress,  $f^\epsilon$ , from interface energy,  $\gamma^\epsilon$ , under applied strain  $\epsilon$  [5]:

$$f^\epsilon = \gamma^\epsilon + \frac{\partial \gamma^\epsilon}{\partial \epsilon} \quad (1)$$

Interface stress,  $f^\epsilon$ , from the bilayer in-plane stress,  $\sigma_{Cu/W}^\epsilon$ :

$$f^\epsilon = -\frac{\lambda^\epsilon}{2} \sigma_{Cu/W}^\epsilon \quad (2)$$

where  $\lambda$  is the bilayer thickness. In experiments, this equation becomes:

$$\sigma_{SC} - \langle \sigma \rangle_{XRD} = \frac{2f}{\lambda} \quad (3)$$

where  $\langle \sigma \rangle_{XRD}$  is the average stress in the Cu and W layers and  $\sigma_{SC}$  is the stress measured from the curvature of the substrate.

## CONCLUSIONS

- The Cu/W interface stress can be tuned non-linearly from positive to negative by changing the Ar pressure during the deposition of nanomultilayers.
- From DFT calculations, we observe that the change of the interface energy with increasing applied stress is associated with the sharp movement of Cu atoms at the interface and changes in interplanar distances.
- Both derivations of the interface stress only match near zero in-plane strain/average stress, which indicates that Eqs. 2-3 need to be revised to account for high in-plane strain.

## ACKNOWLEDGEMENTS

We thank SNSF and Empa Directory Board for financial support and CSCS for providing computing resources. We also thank Aleksandr V. Druzhinin and Lars P.H. Jeurgens for insightful discussions.

## REFERENCES

- [1] A. V. Druzhinin et al., *Materialia* 7, 100400 (2019)
- [2] P. Lazic et al., *Comput. Phys. Commun.* 197, 324 (2015)
- [3] T. D. Kuhne et al., *J. Chem. Phys.* 152 (2020)
- [4] S. Goedecker et al., *Phys. Rev. B* 54, 1703 (1996)
- [5] R. C. Cammarata, *Prog. Surf. Sci.* 46(1), 1–38, (1994).